

IN THE CLAIMS:

1-6. (Cancelled)

7. (Original) A silicon ingot, pulled by a CZ method under conditions satisfying the following (1) and (2):

(1) $1.15 \leq (G1_{edge}/G1_{center}) \leq 1.25$

(2) $0.5 < (\text{OSF ring inner diameter/crystal diameter}) < 1.06 \times (G1_{center} \times G2_{center})^{-0.2}$

8. (Currently Amended) A silicon wafer, cut from the silicon ingot of claim 7, wherein the inner diameter of the OSF ring is at least 1/2 the inner diameter of the wafer and ~~having an oxide film with a withstand voltage a GOIC mode yield is 60% or higher at a C mode ratio.~~

9. (Original) A method of producing a silicon ingot, characterized in that the silicon ingot is pulled by the CZ method under conditions satisfying the following (1) and (2):

(1) $1.15 \leq (G1_{edge}/G1_{center}) \leq 1.25$

(2) $0.5 < (\text{OSF ring inner diameter/crystal diameter}) < 1.06 \times (G1_{center} \times G2_{center})^{-0.2}$

10. (Currently Amended) A silicon wafer for non-annealing, cut from the silicon ingot of claim 7, wherein the inner diameter of OSF ring is at least 1/2 a wafer inner diameter and ~~having an oxide film with a withstand voltage a GOIC mode yield is 60% or higher at a C mode ratio.~~

11-13. (Canceled)

Serial No. 09/856,209

14. (Currently Amended) The silicon wafer for non-annealing according to claim 10, wherein the silicon ingot has a density of void defects existing on the inside of an ~~oxidation-induced stacking fault~~ OSE ring reduced by expanding the inner diameter of the ~~oxidation-induced stacking fault~~ OSE ring.

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15. (Canceled)
